Diode Semiconductor Device - Page 1 of 1



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Inclosure	Material:
Metal	
Overall L	ength:
0.198 incl	hes
Overall D	Diameter:
0.120 incl	hes
Function	For Which Designed:
Special p	urpose
Mounting	g Facility Quantity:
1	
Mounting	g Method:
Threaded	stud
Thready	Qty Per Inch (tpi):
48	
Thread S	ize:
0.099 incł	nes
Semicon	ductor Material:
Silicon	
Voltage F	Rating In Volts Per Characteristic:
1.1 forwa	ard voltage, dc and 75.0 breakdown voltage, dc and 100.0 breakdown voltage, dc
Current F	Rating Per Characteristic:
20.00 nar	noamperes forward current, average peak
Maximun	n Operating Tempurature Per Measurement Point:
175.0 deg	prees celsius ambient air
Thread S	eries Designator:
Unc	
Terminal	Type And Quantity:
1 case an	d 1 threaded stud
Shelf Life	e:
N/a	
Unit Of M	leasure:
Demilitar	ization:
No	
Fiig:	
A110a0	